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BGA7027

400 MHz to 2700 MHz 0.5 W high linearity silicon amplifier

Rev. 2 — 26 November 2010

Product data sheet

1. Product profile

1.1 General description

The BGA7027 MMIC is a one-stage amplifier, offered in a low-cost surface-mount package. It delivers 28 dBm output power at 1 dB gain compression and a superior performance up to 2700 MHz.

1.2 Features and benefits

- 400 MHz to 2700 MHz frequency operating range
- 11 dB small signal gain at 2 GHz
- 28 dBm output power at 1 dB gain compression
- Integrated active biasing
- External matching allows broad application optimization of the electrical performance
- 5 V single supply operation
- ESD protection at all pins

1.3 Applications

- Broadband CPE/MoCA
- WLAN/ISM/RFID
- Wireless infrastructure (base station, repeater, backhaul systems)
- Industrial applications
- E-metering
- Satellite Master Antenna TV (SMATV)

1.4 Quick reference data

Table 1. Quick reference data

Input and output impedances matched to 50 Ω . Typical values at: V_{CC} = 5 V; T_{case} = 25 $^{\circ}$ C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f	frequency		<u>[1]</u> 400	-	2700	MHz
Gp	power gain	f = 2140 MHz	9.0	11.0	13.0	dB
P _{L(1dB)}	output power at 1 dB gain compression	f = 2140 MHz	26	28	-	dBm
IP3 _O	output third-order intercept point	f = 2140 MHz	[2] 40.0	42.5	-	dBm

^[1] Operation outside this range is possible but not guaranteed.



^[2] $P_L = 17$ dBm per tone; spacing = 1 MHz.

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2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	$V_{CC(RF)}$	<u>[1]</u>	
2	GND	[2]	2
3	RF_IN	[1] 3 2 1	3 — 1 2 /// sym130

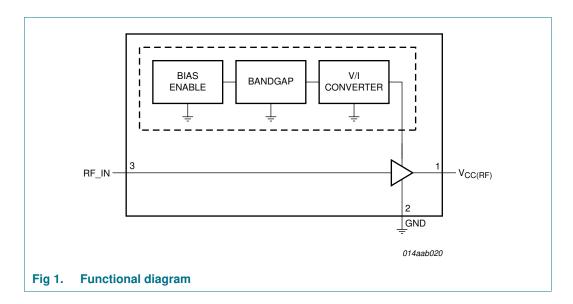
- [1] This pin is DC-coupled and requires an external DC-blocking capacitor.
- [2] The center metal base of the SOT89 also functions as heatsink for the power amplifier.

3. Ordering information

Table 3. Ordering information

Type number	ber Package								
	Name	Description	Version						
BGA7027	-	plastic surface-mounted package; exposed die pad for good heat transfer; 3 leads	SOT89						

4. Functional diagram



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5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			-	5.7	V
$P_{i(RF)}$	RF input power	f = 2140 MHz; switched	[1]	-	28	dBm
T _{case}	case temperature			-40	+85	°C
Tj	junction temperature			-	150	°C
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM); according to JEDEC standard 22-A114E		-	2000	V
		Charged Device Model (CDM); according to JEDEC standard 22-C101B		-	500	V

^[1] Withstands switching between zero and maximum $P_{i(RF)}$

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 85 ^{\circ}\text{C}; V_{CC} = 5 ^{\circ}\text{V}; I_{CC} = 165 ^{\circ}\text{mA}$	38	K/W

7. Static characteristics

 Table 6.
 Static characteristics

Input and output impedances matched to 50 Ω . Typical values at $T_{\rm case}$ = 25 $^{\circ}$ C, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		-	5.0	-	V
I_{CC}	supply current	$V_{CC} = 5.0 \text{ V}$	140	165	190	mA

8. Dynamic characteristics

Table 7. Dynamic characteristics

Input and output impedances matched to 50 Ω . Typical values at V_{CC} = 5 V; T_{case} = 25 $^{\circ}$ C, NXP application circuit; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
f	frequency		[1]	400	-	2700	MHz
G _p	power gain	f = 940 MHz	[2]	-	19.0	-	dB
		f = 1960 MHz	[2]	-	11.5	-	dB
		f = 2140 MHz	[2]	9.0	11.0	13.0	dB

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 Table 7.
 Dynamic characteristics ...continued

Input and output impedances matched to 50 Ω . Typical values at V_{CC} = 5 V; T_{case} = 25 $^{\circ}$ C, NXP application circuit; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P _{L(1dB)}	output power at 1 dB gain	f = 940 MHz	-	29.0	-	dBm
	compression	f = 1960 MHz	-	27.5	-	dBm
		f = 2140 MHz	26.0	28.0	-	dBm
IP3 _O	output third-order intercept point	f = 940 MHz	[3] _	41.5	-	dBm
		f = 1960 MHz	[3] _	43.0	-	dBm
		f = 2140 MHz	[3] 40.0	42.5	-	dBm
NF	noise figure	f = 940 MHz	-	2.6	-	dB
		f = 1960 MHz	-	3.8	-	dB
		f = 2140 MHz	-	3.9	-	dB
RLin	input return loss	f = 940 MHz	[2] _	-16	-	dB
		f = 1960 MHz	[2] _	-8	-	dB
		f = 2140 MHz	[2] _	-8	-	dB
RLout	output return loss	f = 940 MHz	[2] _	-11	-	dB
		f = 1960 MHz	[2] _	-13	-	dB
		f = 2140 MHz	[2] _	-15	-	dB

^[1] Operation outside this range is possible but not guaranteed.

9. Scattering parameters

Table 8. Scattering parameters, MMIC only $V_{CC} = 5 \ V$; $I_{CC} = 165 \ mA$; $T_{case} = 25 \ ^{\circ}C$.

f (MHz)	(MHz) S ₁₁		s ₂₁		S ₁₂		S ₂₂	
	Magnitude (ratio)	Angle (degree)	Magnitude (ratio)	Angle (degree)	Magnitude (ratio)	Angle (degree)	Magnitude (ratio)	Angle (degree)
400	0.92	178	8.03	93	0.01	49	0.76	-176
500	0.92	176	6.55	89	0.01	53	0.75	-178
600	0.92	173	5.55	85	0.02	55	0.75	179
700	0.92	171	4.80	82	0.02	56	0.75	177
800	0.92	168	4.24	79	0.02	56	0.75	175
900	0.92	165	3.80	76	0.02	56	0.75	173
1000	0.92	162	3.46	72	0.03	55	0.76	170
1100	0.92	160	3.14	69	0.03	54	0.76	167
1200	0.92	157	2.85	66	0.03	53	0.76	165
1300	0.92	154	2.61	63	0.03	52	0.76	163
1400	0.93	152	2.39	61	0.03	50	0.77	161
1500	0.93	150	2.20	58	0.03	49	0.78	160
1600	0.93	149	2.03	56	0.04	48	0.78	159
1700	0.93	148	1.88	54	0.04	47	0.79	157

3GA7027

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^[2] Defined at $P_{i(RF)} = -40$ dBm; small signal conditions.

^[3] $P_L= 17 dBm per tone; spacing = 1 MHz.$

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 Table 8.
 Scattering parameters, MMIC only ...continued

 $V_{CC} = 5 \text{ V; } I_{CC} = 165 \text{ mA; } T_{case} = 25 \text{ °C.}$

f (MHz)	s ₁₁		s ₂₁	s ₂₁		s ₁₂		S ₂₂		
	Magnitude (ratio)	Angle (degree)								
1800	0.94	147	1.75	63	0.04	47	0.80	157		
1900	0.94	146	1.64	51	0.04	46	0.80	157		
2000	0.94	146	1.53	50	0.04	46	0.80	157		
2100	0.93	146	1.45	49	0.04	46	0.81	157		
2200	0.93	147	1.39	49	0.05	46	0.81	157		
2300	0.93	147	1.33	48	0.05	45	0.81	158		
2400	0.92	147	1.29	48	0.05	45	0.80	159		
2500	0.91	147	1.26	47	0.05	45	0.80	160		
2600	0.91	148	1.24	46	0.06	45	0.80	160		
2700	0.89	147	1.23	45	0.06	44	0.79	161		

10. Reliability information

Table 9. Reliability

Life test	Conditions	Intrinsic failure rate
HTOL	according to JESD85; confidence level 60 %; T_j = 55 °C; activation energy = 0.7 eV; acceleration factor determined according to the Arrhenius equation	4

11. Moisture sensitivity

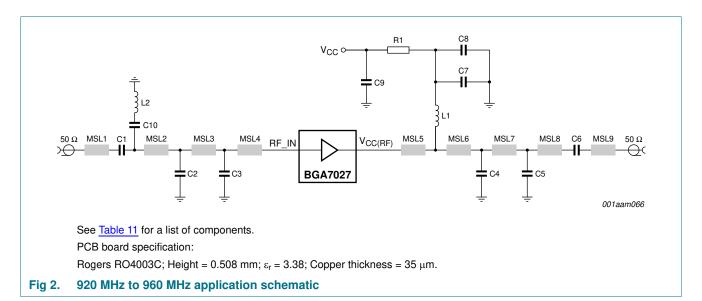
Table 10. Moisture sensitivity level

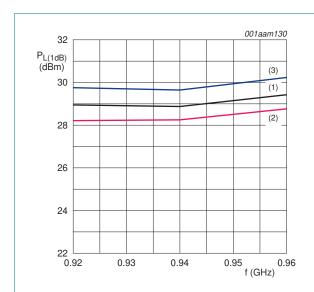
Test methodology	Class
JESD-22-A113	1

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12. Application information

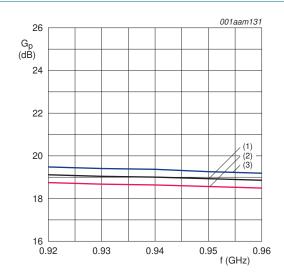
12.1 920 MHz to 960 MHz





- (1) $T_{case} = 25 \, ^{\circ}C$.
- (2) $T_{case} = 85 \, ^{\circ}C$.
- (3) $T_{case} = -40 \, ^{\circ}C$.

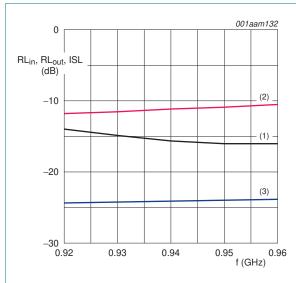
Fig 3. Output power at 1 dB gain compression as a function of frequency



- (1) $T_{case} = 25 \, ^{\circ}C$.
- (2) $T_{case} = 85 \, ^{\circ}C$.
- (3) $T_{case} = -40 \, ^{\circ}C$.

Fig 4. Power gain as a function of frequency

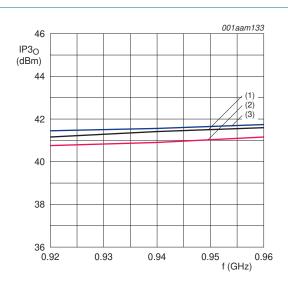
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T_{case} = 25 °C.

- (1) RL_{in}.
- (2) RLout.
- (3) ISL.

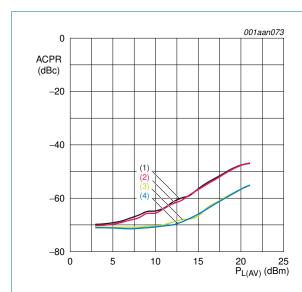
Fig 5. Input return loss, output return loss and isolation as a function of frequency



 $P_1 = 17 \text{ dBm}$; tone spacing = 1 MHz

- (1) $T_{case} = 25 \, ^{\circ}C$.
- (2) $T_{case} = 85 \, ^{\circ}C$.
- (3) $T_{case} = -40 \, ^{\circ}C$.

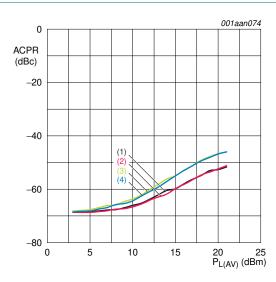
Fig 6. Output third-order intercept point as a function of frequency



2-carrier W-CDMA; each carrier according to 3GPP test model 1; 64 DPCH; PAR for composite signal = 7.5 dB; 5 MHz carrier spacing.

- (1) f = 920 MHz; ACPR measured at $f \pm 5 \text{ MHz}$
- (2) f = 960 MHz; ACPR measured at $f \pm 5 \text{ MHz}$
- (3) f = 920 MHz; ACPR measured at $f \pm 10$ MHz
- (4) f = 960 MHz; ACPR measured at $f \pm 10 \text{ MHz}$

Fig 7. Adjacent channel power ratio as a function of average output power

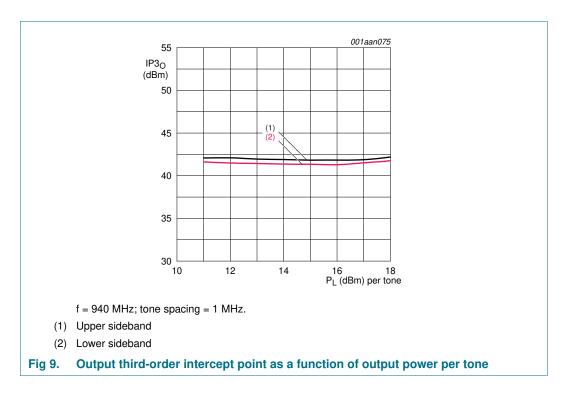


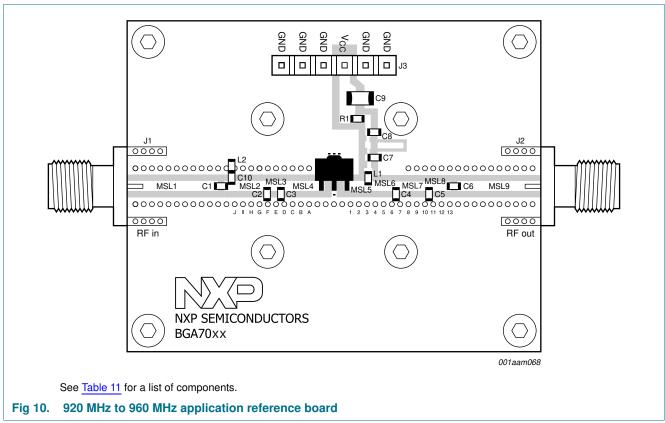
2-carrier W-CDMA; each carrier according to 3GPP test model 1; 64 DPCH; PAR for composite signal = 9 dB; 10 MHz carrier spacing.

- (1) f = 920 MHz; ACPR measured at $f \pm 5 \text{ MHz}$
- (2) f = 960 MHz; ACPR measured at $f \pm 5 \text{ MHz}$
- (3) f = 920 MHz; ACPR measured at $f \pm 10$ MHz
- (4) f = 960 MHz; ACPR measured at $f \pm 10 \text{ MHz}$

Fig 8. Adjacent channel power ratio as a function of average output power

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Table 11. List of components of 920 MHz to 960 MHz

See <u>Figure 2</u> and <u>Figure 10</u> for component layout.

Printed-Circuit Board (PCB): Rogers RO4003C stack; height = 0.508 mm; copper plating thickness = $35 \mu m$.

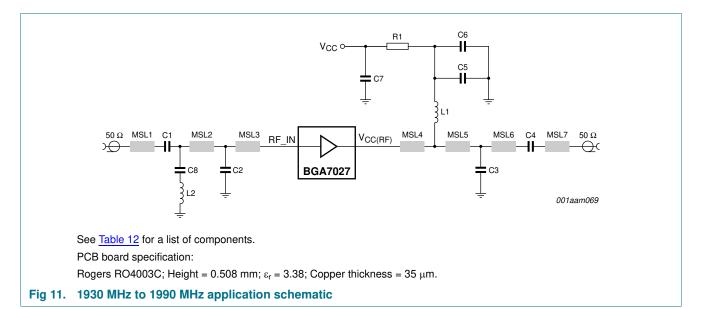
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Component	Description	Value	Function	Remarks
C1, C6	capacitor	68 pF	DC blocking	Murata, GRM1885C1H680JA01D
C2	capacitor	5.6 pF	input match	Murata, GRM1885C1H5R6CZ01D
C3	capacitor	2.7 pF	input match	Murata, GRM1885C1H2R7CZ01D
C4	capacitor	1.0 pF	output match	Murata, GRM1885C1H1R0CZ01D
C5	capacitor	3.9 pF	output match	Murata, GRM1885C1H3R9CZ01D
C7	capacitor	68 pF	RF decoupling	Murata, GRM1885C1H680JA01D
C8	capacitor	100 nF	LF decoupling	AVX, 0603YC104KAT2A
C9	capacitor	10 μF	LF decoupling	AVX, 1206ZG106ZAT2A
C10	capacitor	68 nF	IMD3 suppression	Murata, GRM1888R71H683KA93D
J1, J2	RF connector	SMA		Emerson Network Power, 142-0701-841
J3	DC connector	6 pins		MOLEX
L1	inductor	22 nH	DC Feed	Tyco Electronics, 36501J022JTDG
L2[1]	inductor	33 nH	IMD3 suppression	Tyco Electronics, 36501J033JTDG
MSL1 ²	micro stripline	1.14 mm × 0.8 mm × 10.95 mm	input match	
MSL2[2]	micro stripline	1.14 mm \times 0.8 mm \times 4.3 mm	input match	
MSL3[2]	micro stripline	1.14 mm \times 0.8 mm \times 1.7 mm	input match	
MSL4[2]	micro stripline	$1.14~\text{mm} \times 0.8~\text{mm} \times 4.8~\text{mm}$	input match	
MSL5[2]	micro stripline	$1.14~\text{mm} \times 0.8~\text{mm} \times 2.7~\text{mm}$	output match	
MSL6[2]	micro stripline	$1.14~\text{mm} \times 0.8~\text{mm} \times 3.2~\text{mm}$	output match	
MSL7[2]	micro stripline	$1.14~\text{mm} \times 0.8~\text{mm} \times 4.0~\text{mm}$	output match	
MSL8[2]	micro stripline	1.14 mm \times 0.8 mm \times 1.6 mm	output match	
MSL9[2]	micro stripline	1.14 mm \times 0.8 mm \times 10.95 mm	output match	
R1	resistor	0 Ω		Multicomp, MC 0.063W 0603 0R

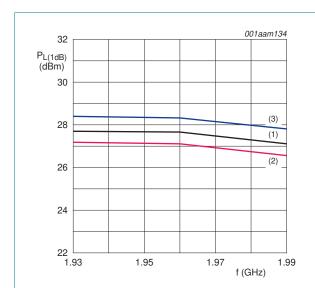
^[1] Low Q inductor.

^[2] MSL1 to MSL9 dimensions are specified as Width (W), Spacing (S) and Length (L).

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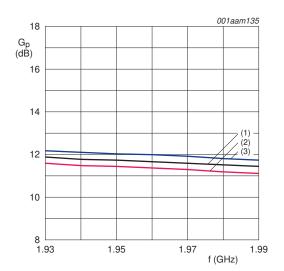
12.2 1930 MHz to 1990 MHz





- (1) $T_{case} = 25 \, ^{\circ}C$.
- (2) $T_{case} = 85 \, ^{\circ}C$.
- (3) $T_{case} = -40 \, ^{\circ}C$.

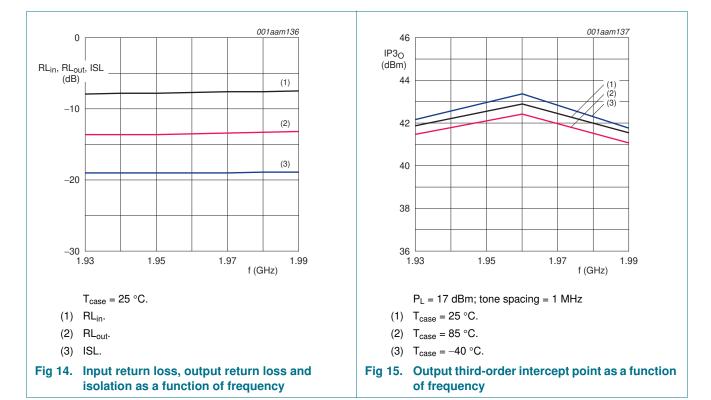
Fig 12. Output power at 1 dB gain compression as a function of frequency

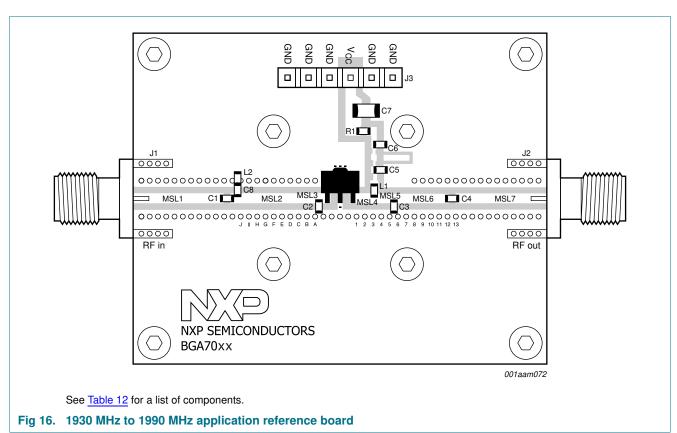


- (1) $T_{case} = 25 \, ^{\circ}C$.
- (2) $T_{case} = 85 \, ^{\circ}C$.
- (3) $T_{case} = -40 \, ^{\circ}C$.

Fig 13. Power gain as a function of frequency

400 MHz to 2700 MHz 0.5 W high linearity silicon amplifier





400 MHz to 2700 MHz 0.5 W high linearity silicon amplifier

Table 12. List of components of 1930 MHz to 1990 MHz

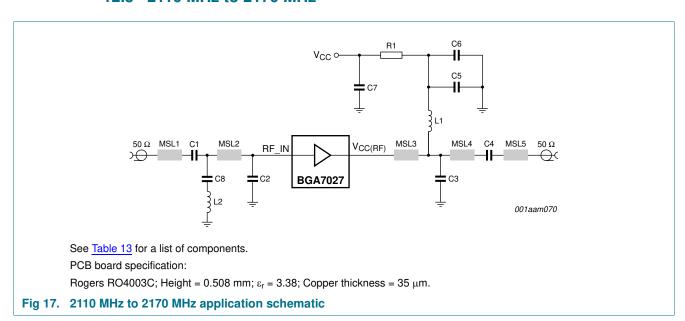
See Figure 11 and Figure 16 for component layout.

Printed-Circuit Board (PCB): Rogers RO4003C stack; height = 0.508 mm; copper plating thickness = 35 μ m.

0	Danadatian	Valera	Francisco.	Damania
•	Description	Value	Function	Remarks
C1, C4	capacitor	15 pF	DC blocking	Murata, GRM1885C1H150JA01D
C2	capacitor	2.4 pF	input match	Murata, GRM1885C1H2R4CZ01D
C3	capacitor	2.0 pF	output match	Murata, GRM1885C1H2R0CZ01D
C5	capacitor	15 pF	RF decoupling	Murata, GRM1885C1H150JA01D
C6	capacitor	100 nF	LF decoupling	AVX, 0603YC104KAT2A
C7	capacitor	10 μF	LF decoupling	AVX, 1206ZG106ZAT2A
C8	capacitor	68 nF	IMD3 suppression	Murata, GRM1888R71H683KA93D
J1, J2	RF connector	SMA		Emerson Network Power, 142-0701-841
J3	DC connector	6 pins		MOLEX
L1	inductor	22 nH	DC Feed	Tyco Electronics, 36501J022JTDG
L2[1]	inductor	33 nH	IMD3 suppression	Tyco Electronics, 36501J033JTDG
MSL1 ²	micro stripline	1.14 mm \times 0.8 mm \times 10.95 mm	input match	
MSL2[2]	micro stripline	$1.14~\text{mm} \times 0.8~\text{mm} \times 10.6~\text{mm}$	input match	
MSL3[2]	micro stripline	$1.14~\text{mm} \times 0.8~\text{mm} \times 1.0~\text{mm}$	input match	
MSL4 ²	micro stripline	$1.14~\text{mm} \times 0.8~\text{mm} \times 2.7~\text{mm}$	output match	
MSL5[2]	micro stripline	1.14 mm \times 0.8 mm \times 2.0 mm	output match	
MSL6[2]	micro stripline	1.14 mm \times 0.8 mm \times 6.8 mm	output match	
MSL7 ^[2]	micro stripline	1.14 mm \times 0.8 mm \times 10.95 mm	output match	
R1	resistor	0 Ω		Multicomp. MC 0.063W 0603 0R

^[1] Low Q inductor.

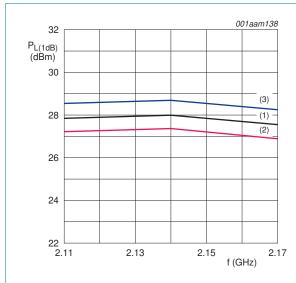
12.3 2110 MHz to 2170 MHz



BGA7027

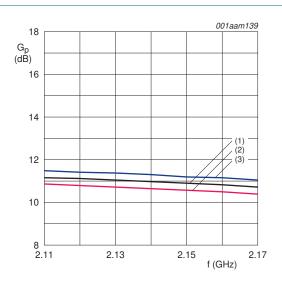
^[2] MSL1 to MSL7 dimensions are specified as Width (W), Spacing (S) and Length (L).

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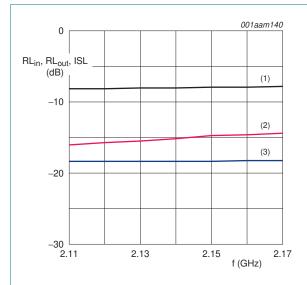
- (1) $T_{case} = 25 \, ^{\circ}C$.
- (2) $T_{case} = 85 \, ^{\circ}C$.
- (3) $T_{case} = -40 \, ^{\circ}C$.

Fig 18. Output power at 1 dB gain compression as a function of frequency



- (1) $T_{case} = 25 \, ^{\circ}C$.
- (2) $T_{case} = 85 \, ^{\circ}C$.
- (3) $T_{case} = -40 \, ^{\circ}C$.

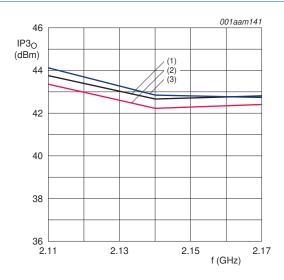
Fig 19. Power gain as a function of frequency



 $T_{case} = 25 \, ^{\circ}C.$

- (1) RL_{in}.
- (2) RLout.
- (3) ISL.

Fig 20. Input return loss, output return loss and isolation as a function of frequency

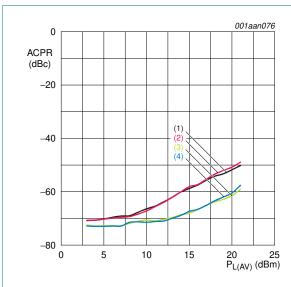


 $P_L = 17 \text{ dBm}$; tone spacing = 1 MHz

- (1) $T_{case} = 25 \, ^{\circ}C$.
- (2) $T_{case} = 85 \, ^{\circ}C$.
- (3) $T_{case} = -40 \, ^{\circ}C$.

Fig 21. Output third-order intercept point as a function of frequency

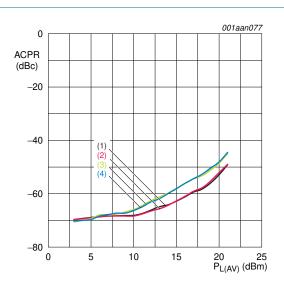
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2-carrier W-CDMA; each carrier according to 3GPP test model 1; 64 DPCH; PAR for composite signal = 7.5 dB; 5 MHz carrier spacing.

- (1) f = 2110 MHz; ACPR measured at $f \pm 5 \text{ MHz}$
- (2) f = 2170 MHz; ACPR measured at $f \pm 5 \text{ MHz}$
- (3) f = 2110 MHz; ACPR measured at $f \pm 10 \text{ MHz}$
- (4) f = 2170 MHz; ACPR measured at $f \pm 10$ MHz

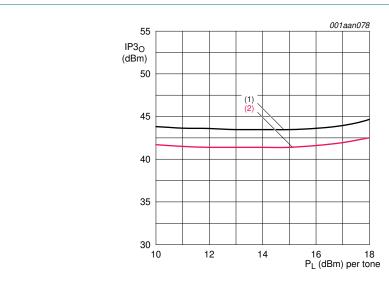
Fig 22. Adjacent channel power ratio as a function of average output power



2-carrier W-CDMA; each carrier according to 3GPP test model 1; 64 DPCH; PAR for composite signal = 9 dB; 10 MHz carrier spacing.

- (1) f = 2110 MHz; ACPR measured at $f \pm 5 \text{ MHz}$
- (2) f = 2170 MHz; ACPR measured at $f \pm 5 \text{ MHz}$
- (3) f = 2110 MHz; ACPR measured at $f \pm 10 \text{ MHz}$
- (4) f = 2170 MHz; ACPR measured at $f \pm 10 \text{ MHz}$

Fig 23. Adjacent channel power ratio as a function of average output power

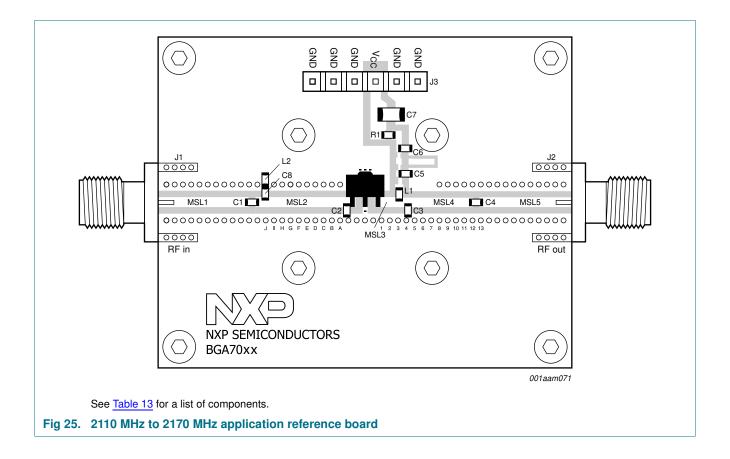


f = 2140 MHz; tone spacing = 1 MHz.

- (1) Upper sideband
- (2) Lower sideband

Fig 24. Output third-order intercept point as a function of output power per tone

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Table 13. List of components of 2110 MHz to 2170 MHz

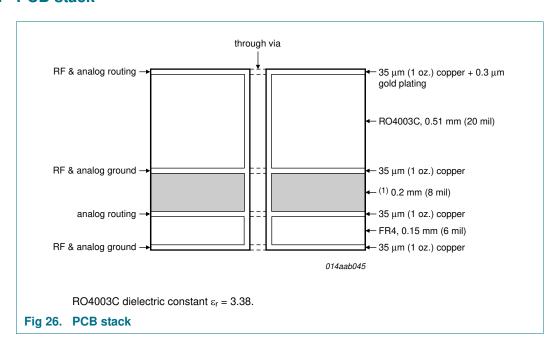
See Figure 17 and Figure 25 for component layout.

Printed-Circuit Board (PCB): Rogers RO4003C stack; height = 0.508 mm; copper plating thickness = 35 μm.

	, ,			,
Component	Description	Value	Function	Remarks
C1, C4	capacitor	15 pF	DC blocking	Murata, GRM1885C1H150JA01D
C2	capacitor	2.2 pF	input match	Murata, GRM1885C1H2R2CZ01D
C3	capacitor	2.0 pF	output match	Murata, GRM1885C1H1R0CZ01D
C5	capacitor	15 pF	RF decoupling	Murata, GRM1885C1H150JA01D
C6	capacitor	100 nF	LF decoupling	AVX, 0603YC104KAT2A
C7	capacitor	10 μF	LF decoupling	AVX, 1206ZG106ZAT2A
C8	capacitor	68 nF	IMD3 suppression	Murata, GRM1888R71H683KA92D
J1, J2	RF connector	SMA		Emerson Network Power, 142-0701-841
J3	DC connector	6 pins		MOLEX
L1	inductor	22 nH	DC Feed	Tyco Electronics, 36501J022JTDG
L2[1]	inductor	33 nH	IMD3 suppression	Tyco Electronics, 36501J033JTDG
MSL1 ²	micro stripline	1.14 mm \times 0.8 mm \times 10.95 mm	input match	
MSL2[2]	micro stripline	1.14 mm \times 0.8 mm \times 11.3 mm	input match	
MSL3[2]	micro stripline	1.14 mm \times 0.8 mm \times 3.2 mm	output match	
MSL4[2]	micro stripline	1.14 mm \times 0.8 mm \times 8.0 mm	output match	
MSL5[2]	micro stripline	1.14 mm \times 0.8 mm \times 10.95 mm	output match	
R1	resistor	0 Ω		Multicomp, MC 0.063W 0603 0R

^[1] Low Q inductor.

12.4 PCB stack



^[2] MSL1 to MSL5 dimensions are specified as Width (W), Spacing (S) and Length (L).

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13. Package outline

Plastic surface-mounted package; exposed die pad for good heat transfer; 3 leads

SOT89

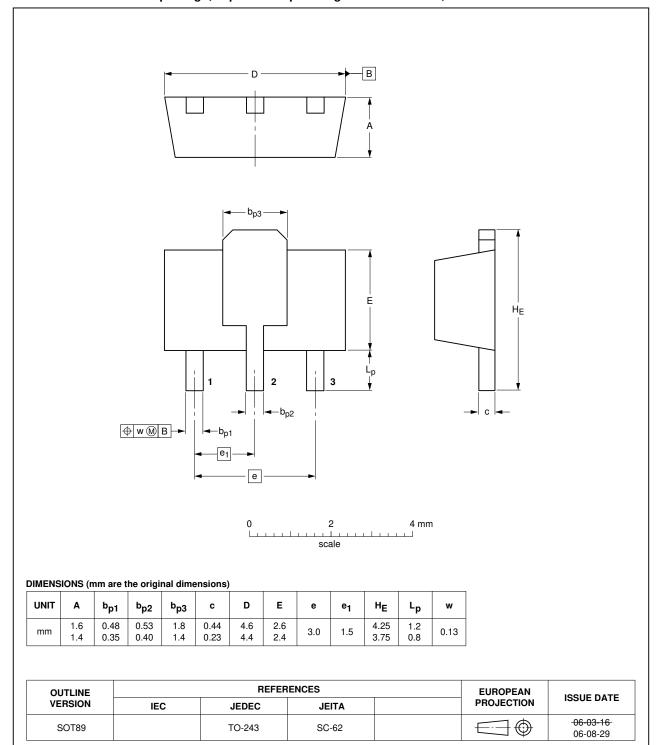


Fig 27. Package outline SOT89

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14. Abbreviations

Table 14. Abbreviations

14510 1 11 715510	
Acronym	Description
3GPP	3rd Generation Partnership Project
CPE	Customer-Premises Equipment
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
HTOL	High Temperature Operating Life
IMD3	3rd-order InterModulation Distortion
ISM	Industrial, Scientific and Medical
MMIC	Monolithic Microwave Integrated Circuit
MoCA	Multimedia over Coax Alliance
RFID	Radio Frequency IDentification
W-CDMA	Wideband Code Division Multiple Access
W-LAN	Wireless Local Area Network

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15. Revision history

Table 15. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGA7027 v.2	20101126	Product data sheet	-	BGA7027 v.1
Modifications:	 Table 1 on Table 4 on Table 5 on Table 7 on Table 7 on Figure 7 on Figure 8 on Figure 9 on Figure 22 o Figure 23 o 	of this data sheet has been bage 1: some values have bage 1: some values have bage 3: data for P _{i(RF)} have bage 3: conditions have bage 3: some values have bage 3: some values have bage 7: figure has been a page 7: figure has been a page 14: figure has been a page 14: figure has been page 14:	been added been added been changed been added dded dded dded n added n added	
BGA7027 v.1	20100811	Preliminary data sheet	-	-

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16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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